

MICRO ELECTRONICS

PN3568
NPN
SILICON
TRANSISTOR

PN3568 is NPN silicon planar epitaxial transistor designed for amplifier and switching applications for collector current up to 500mA.

T0-92



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CB0}	80V
Collector-Emitter Voltage	V_{CE0}	60V
Emitter-Base Voltage	V_{EB0}	5V
Collector Current	I_C	500mA
Total Power Dissipation	P_{tot}	600mW
Operating Junction & Storage Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV_{CB0}	80		V	$I_C=100\mu A$ $I_E=0$
Collector-Emitter Breakdown Voltage	LV_{CE0}	60		V	$I_C=10mA$ $I_B=0^*$
Emitter-Base Breakdown Voltage	BV_{EB0}	5		V	$I_E=10\mu A$ $I_C=0$
Collector Cutoff Current	I_{CB0}		50	nA	$V_{CB}=40V$ $I_E=0$
D.C. Current Gain	HFE	40			$I_C=30mA$ $V_{CE}=1V^*$
		40	120		$I_C=150mA$ $V_{CE}=1V^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25	V	$I_C=150mA$ $I_B=15mA^*$
Output Capacitance	C_{ob}		20	pF	$V_{CB}=10V$ $f=1MHz$
Current Gain-Bandwidth Product	f_T	60	600	MHz	$I_C=50mA$ $V_{CE}=1V$

* Pulse Test : Pulse Width = 300 μ S, Duty Cycle = 2%.

